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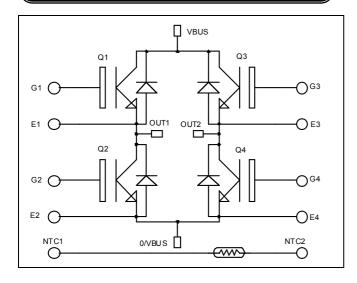








Full - Bridge Trench + Field Stop IGBT3 Power Module



G4 🛭

E4 🛭

E2 (

G2 f

O/VBUS

$$V_{CES} = 1700V$$

 $I_{C} = 50A$ @ $Tc = 80$ °C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

8 G3

₿ E3

VBUS

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
I_{C}	Continuous Collector Current	$T_C = 80$ °C	50	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	312	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	100A @ 1600V	

OUT2

OUT1

NTC2

NTC1

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		2.0	2.4	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 50A$ $T_j = 125^{\circ}$	$T_j = 125$ °C		2.4		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	=0V			400	nA

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit	
C_{ies}	Input Capacitance	$V_{GE} = 0V$		4400			
C_{oes}	Output Capacitance	$V_{CE} = 25V$		180		pF	
C_{res}	Reverse Transfer Capacitance	f = 1MHz		150			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		370			
T_{r}	Rise Time	$V_{GE} = 15V$		40			
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 50A$		650		ns	
T_{f}	Fall Time	$R_G = 10\Omega$		180			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		400			
T_{r}	Rise Time	$V_{GE} = 15V$		50			
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ - $I_C = 50A$		800		ns	
T_{f}	Fall Time	$R_G = 10\Omega$		300			
Eon	Turn-on Switching Energy	$V_{GE} = 15V \ V_{Bus} = 900V$ $T_j = 125^{\circ}C$		16		mJ	
E_{off}	Turn-off Switching Energy	$\begin{bmatrix} I_C = 50A \\ R_G = 10\Omega \end{bmatrix} \qquad T_j = 125^{\circ}C$		15		1113	

Diode ratings and characteristics

Symbol Characteristic

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
Ţ	Mayimayan Dayanga Laakaga Cymmant	V -1700V	$T_j = 25^{\circ}C$			250	1
I_{RM}	Maximum Reverse Leakage Current	$V_{R}=1700V$	$T_j = 125$ °C			500	μA
I_F	DC Forward Current		$Tc = 80^{\circ}C$		50		A
$V_{\rm F}$	Diode Forward Voltage	$I_F = 50A$	$T_j = 25$ °C		1.8	2.2	V
* F	Blode I of ward Voltage	1 _F - 30A	$T_{i} = 125^{\circ}C$		1.9		•
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		ns
чт	reverse receivery Time		$T_{j} = 125^{\circ}C$		490		115
Q_{rr}	Payarga Pagayary Charga	$V_{R} = 900 V$	$T_j = 25^{\circ}C$		14		μС
Qrr	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		23		μС
E_{r}	Reverse Recovery Energy	·	$T_j = 25^{\circ}C$		6		mJ
\mathbf{E}_{r}			$T_{j} = 125^{\circ}C$		12		1117



 $Temperature \ sensor \ NTC \ (see \ application \ note \ APT0406 \ on \ www.microsemi.com \ for \ more \ information).$

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

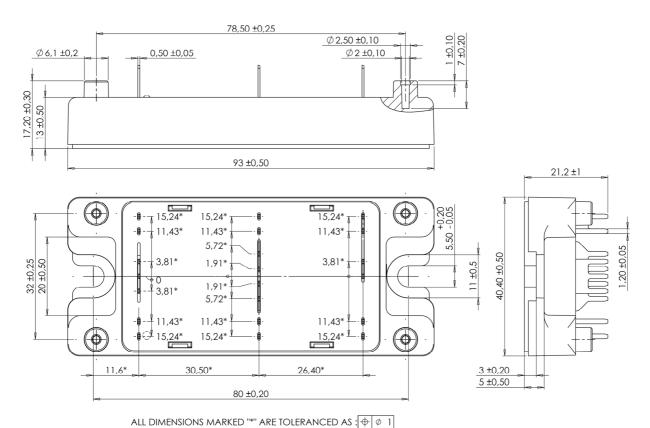
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT Diode			0.4	°C/W
1\(\text{thJC}\)						0.7	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range -40 150		150				
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)

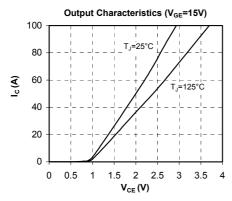


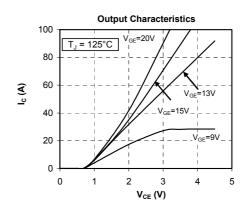
 $See \ application \ note \ APT0501 - Mounting \ Instructions \ for \ SP4 \ Power \ Modules \ on \ www.microsemi.com$

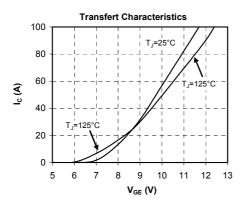
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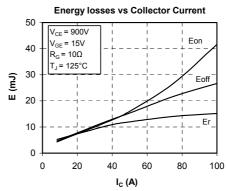


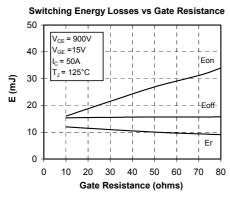
Typical Performance Curve

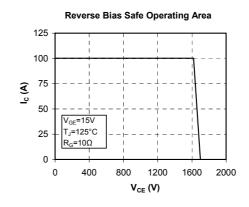


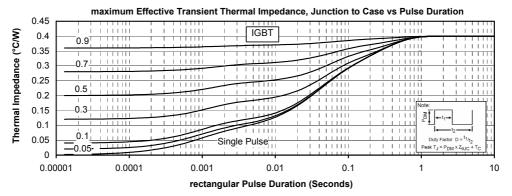




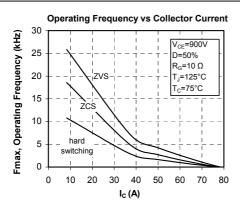


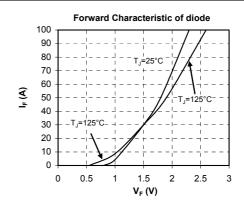


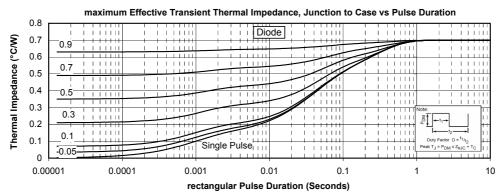












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